

IN THE SPECIFICATION:

Please replace paragraph [0005] with the following:

A1 [0005] During an HF-last rinse of a semiconductor structure with exposed silicon, for example, a significant number of $(\text{Si})_2=\text{O}$ bonds are changed to Si-H bonds. About ten to twenty percent of the changed bonds, however, are Si-F instead of the preferred Si-H. During the industry standard DI water rinse that follows most chemical treatments, the Si-F bonds in this example are easily washed off, and oxidation of semiconductor materials, such as silicon, occurs while transferring the semiconductor structure from a rinsing vessel to a drying vessel. Oxidation can occur both during the transfer to the drying vessel and while the semiconductor structure resides in the drying vessel prior to drying.
